

**WSR200N08** 

N-Ch MOSFET

## **General Description**

The WSR200N08 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSR200N08 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

## **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed •
- Green Device Available •

## **Product Summery**

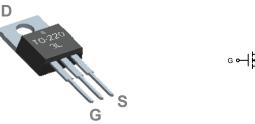
BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
80V	2.9mΩ	200A

## **Applications**

Switching application

Power Management for Inverter Systems.

## **TO-220FB-3L Pin Configuration**



## **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	80	V
V <sub>GS</sub>	Gate-Source Voltage	±25	V
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	200	А
I₀@Tc=100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	144	А
I <sub>DM</sub>	Pulsed Drain Current <sup>2,</sup> T <sub>C</sub> =25°C	790	A
EAS	Avalanche Energy, Single pulse,L=0.5mH	1496	mJ
I <sub>AS</sub>	Avalanche Current, Single pulse,L=0.5mH	200	А
P <sub>D</sub> @T <sub>C</sub> =25℃	Total Power Dissipation <sup>4</sup>	345	W
P <sub>D</sub> @T <sub>C</sub> =100℃	Total Power Dissipation <sup>4</sup>	173	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 175	°C
TJ	Operating Junction Temperature Range	175	°C

## **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>eja</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>		62.5	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>		0.43	°C/W



N-Ch MOSFET

# Electrical Characteristics (T<sub>J</sub>=25 C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	80			V
$\triangle BV_{DSS} / \triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25 $^\circ\!\!{\rm C}$ , $I_D$ = 1mA		0.096		V/℃
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V,I <sub>D</sub> =100A		2.9	3.5	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage		2.0	3.0	4.0	V
V <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient	VGS-VDS; ID -2500A		-5.5		mV/℃
	Drain Source Lookage Current	$V_{\text{DS}}\text{=}80\text{V}$ , $V_{\text{GS}}\text{=}0\text{V}$ , $T_{\text{J}}\text{=}25^\circ\!\text{C}$			1	uA
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{\text{DS}}\text{=}80\text{V}$ , $V_{\text{GS}}\text{=}0\text{V}$ , $T_{\text{J}}\text{=}55^\circ\!\text{C}$			10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm25V$ , $V_{DS}$ =0V			±100	nA
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		3.2		Ω
Qg	Total Gate Charge (10V)			197		
Q <sub>gs</sub>	Gate-Source Charge	$V_{\text{DS}}\text{=}80V$ , $V_{\text{GS}}\text{=}10V$ , $I_{\text{D}}\text{=}30A$		31		nC
Q <sub>gd</sub>	Gate-Drain Charge			75		
T <sub>d(on)</sub>	Turn-On Delay Time			28		
Tr	Rise Time	V <sub>DD</sub> =50V , V <sub>GS</sub> =10V ,		18		
T <sub>d(off)</sub>	Turn-Off Delay Time	R <sub>G</sub> =3Ω, I <sub>D</sub> =30A		42		ns
T <sub>f</sub>	Fall Time			54		
C <sub>iss</sub>	Input Capacitance			8154		
C <sub>oss</sub>	Output Capacitance	out Capacitance V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		1029		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			650		

## **Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions		Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy $^5$	V <sub>DD</sub> =25V , L=0.5mH , I <sub>AS</sub> =28A	160			mJ

# **Diode Characteristics**

Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>				200	А
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>	$V_G=V_D=0V$ , Force Current			350	А
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =15A , TJ=25℃			1.2	V
t <sub>rr</sub>	Reverse Recovery Time			30		nS
Qrr	Reverse Recovery Charge	IF=15A,dI/dt=100A/µs,TJ=25℃		52		nC

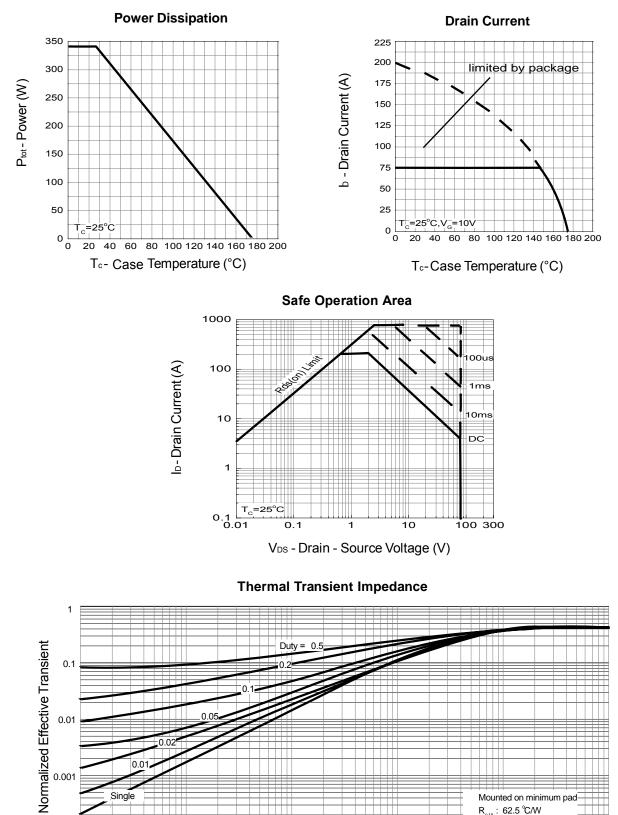
Note \* : Pulse test ; pulse width  $\leq$ 300 $\mu$ s, duty cycle $\leq$ 2%.



**WSR200N08** 

**N-Ch MOSFET** 

# **Typical Operating Characteristics**



0.0001 0.0001 Single

0.001

0.1

0.01

Square Wave Pulse Duration (sec)

10

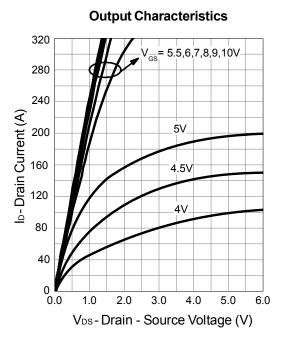
Mounted on minimum pad-R<sub>₀JA</sub>: 62.5 ℃/W

1

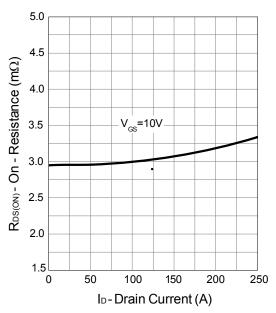


**N-Ch MOSFET** 

# **Typical Operating Characteristics (Cont.)**



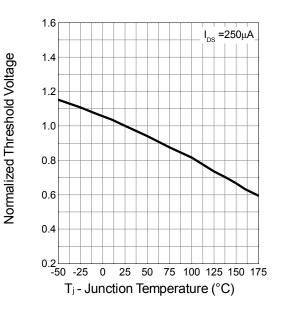
Drain-Source On Resistance



14 I<sub>DS</sub>=100A 12  $R_{DS(ON)}$  - On - Resistance (m $\Omega$ ) 10 8 6 4 2 0 ∟ 3 4 5 6 7 8 9 10 V<sub>GS</sub> - Gate - Source Voltage (V)

**Gate-Source On Resistance** 

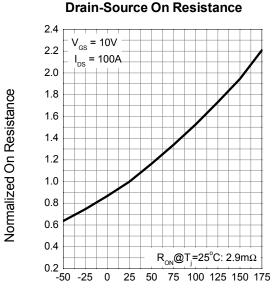
Gate Threshold Voltage





**N-Ch MOSFET** 

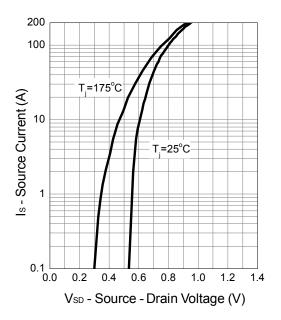
# **Typical Operating Characteristics (Cont.)**



T<sub>j</sub>-Junction Temperature (°C)

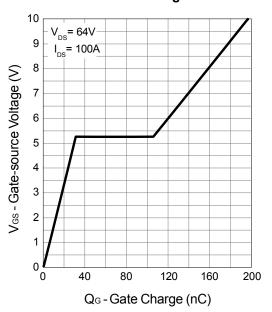
Capacitance

## Source-Drain Diode Forward



12000 Frequency=1MHz 10500 9000 Ciss 5000 7500 6000 4500 0 3000 Coss 1500 Crss 0 L 0 8 16 24 32 40 V<sub>DS</sub> - Drain - Source Voltage (V)

Gate Charge



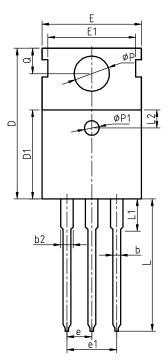


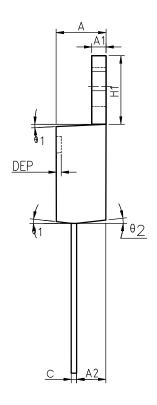
WSR200N08

N-Ch MOSFET

# Package Information TO-220AB

# TO-220FB-3L





COMMON DIMENSIONS

	I		
ΠΠ			
•	E2	-	

SYMBOL	MI N	NOM	MAX	MI N	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
С	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
Ε	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
е		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
Р	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
θ 1	5°	<b>7</b> °	9°	5°	<b>7</b> °	9°
θ2	<b>1</b> °	3°	5°	<b>1</b> °	3°	5°
θ3	<b>1</b> °	3°	5°	<b>1</b> °	3°	5°



# Attention

1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.

2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.

3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

5, In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.

7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.

9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.